

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8	SiC near3 single adj crystal same gate adj (insulati\$2 or dielectric or oxide or nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 19:11
L2	1	SiC near3 single adj crystalline same gate adj (insulati\$2 or dielectric or oxide or nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 19:35
S1	430	gate adj (insulation or insulating) same (krypton or kr)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/04 20:38
S2	10	S1 and siC near2 (substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/04 20:41
S3	10	S1 and siC near3 (substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/04 20:41
S4	10	S1 and SiC near3 (substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/04 20:43
S5	1466	gate adj (insulation or insulating) same (argon or Ar)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/04 20:44

S6	36	S5 and SiC near3 (substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/04 20:45
S7	4	S5 and SiC near3 (substrate or wafer) same plasma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/04 21:17
S8	435	gate adj (insulation or insulating) same (xenon or Xe)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/04 21:20
S9	45	S8 and SiC	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/04 21:21
S10	45	S8 and SiC and plasma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/04 21:21
S14	36	(insulation or insulating) adj (film or layer) same plasma same (Kr or krypton or Ar or argon or Xe or xenon) same SiC	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/05 07:26
S15	466	gate near2 (insulation or insulating) adj (film or layer) same plasma same (Kr or krypton or Ar or argon or Xe or xenon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/05 07:41
S16	467	gate near1 (insulation or insulating) adj (film or layer) same plasma same (Kr or krypton or Ar or argon or Xe or xenon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/05 07:41
S17	1	("7226848").PN.	USPAT	OR	OFF	2008/04/06 13:11

S19	1	("6975018").PN.	USPAT	OR	OFF	2008/04/06 13:52
S22	1	("7279066").PN.	USPAT	OR	OFF	2008/04/06 14:13
S24	1	"4027320".PN.	USPAT; USOCR	OR	OFF	2008/04/06 14:14
S25	1	"5034086".PN.	USPAT; USOCR	OR	OFF	2008/04/06 14:15
S26	1	"5889304".PN.	USPAT; USOCR	OR	OFF	2008/04/06 14:17
S27	1	"6497783".PN.	USPAT; USOCR	OR	OFF	2008/04/06 14:17
S28	1	"20030003243".PN.	US-PGPUB	OR	OFF	2008/04/06 14:19
S29	7	SiC near2 substrate same plasma same gate adj (insulation or insulating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/06 14:59
S30	132	SiC near2 substrate same gate adj (insulation or insulating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/06 15:02
S32	10	(SiC near2 Si)near2 substrate same advantage\$1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/06 15:54
S33	690	(SiC near2 Si)near2 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/06 15:57
S34	525	(SiC or silicon adj carbide)near2 substrate same plasma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/06 17:04

S35	15	(SiC or silicon adj carbide) near2 substrate same plasma with (insulation or insulating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/06 17:05
S36	1	("6208012").PN.	USPAT	OR	OFF	2008/04/06 18:41
S37	1	("6028012").PN.	USPAT	OR	OFF	2008/04/06 18:42
S38	7	("4788082" "5562952" "5597744" "5614749" "5656516" "5789311" "5796122").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/04/06 18:42
S39	250	(SiC or silicon adj carbide) near2 substrate same gate adj (insulation or insulating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/06 18:49
S40	9	(SiC or silicon adj carbide) near2 substrate same gate adj (insulation or insulating) same plasma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/07 08:38
S43	12	(SiC or silicon adj carbide) near2 substrate same gate near2 (insulation or insulating) same plasma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/07 08:44
S44	1	("6399520").PN.	USPAT	OR	OFF	2008/04/07 09:10
S45	1	("7122488").PN.	USPAT	OR	OFF	2008/04/07 10:09
S46	7	("20030059556" "20040129673" "4888820" "5135885" "6136727" "6437371" "6482704").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/04/07 10:10
S47	1	("5135885").PN.	USPAT	OR	OFF	2008/04/07 10:21

S48	1	S47 and (argon or Ar)	USPAT	OR	OFF	2008/04/07 10:21
S51	2	"20040129673"	US-PGPUB; USPAT	OR	OFF	2008/04/07 10:28
S53	1	("6975018").PN.	USPAT	OR	OFF	2008/04/07 10:56
S55	431	gate adj (insulation or insulating) same (krypton or kr)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/12 00:12
S56	155	gate adj (insulation or insulating) same (krypton or kr)	USPAT	OR	OFF	2008/04/12 00:12
S57	1	("5972801").PN.	USPAT	OR	OFF	2008/04/12 00:50

4/12/08 7:46:53 PM

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